

TO-92L Plastic-Encapsulate Transistors

2SD667,2SD667A TRANSISTOR (NPN)

FEATURES

- Low Frequency Power Amplifier
- Complementary Pair with 2SB647/A

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector- Base Voltage	120	V
V _{CEO}	Collector-Emitter Voltage 2SD667	80	
	2SD667A	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _c	Collector Current -Continuous	1	A
P _c	Collector Power Dissipation	900	mW
R _{θJA}	Thermal Resistance Junction to Ambient	139	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

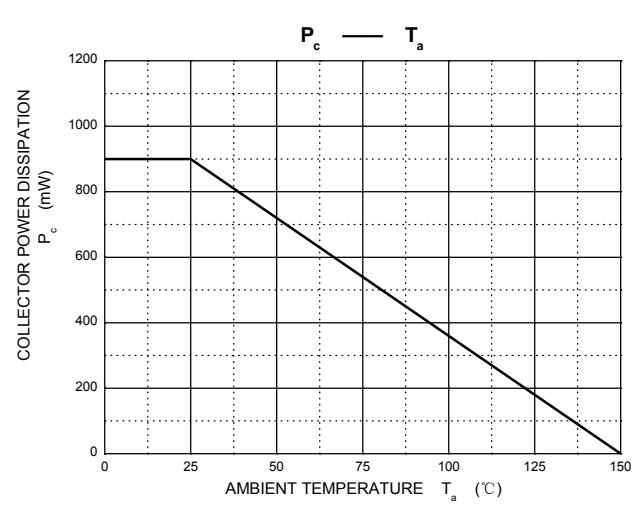
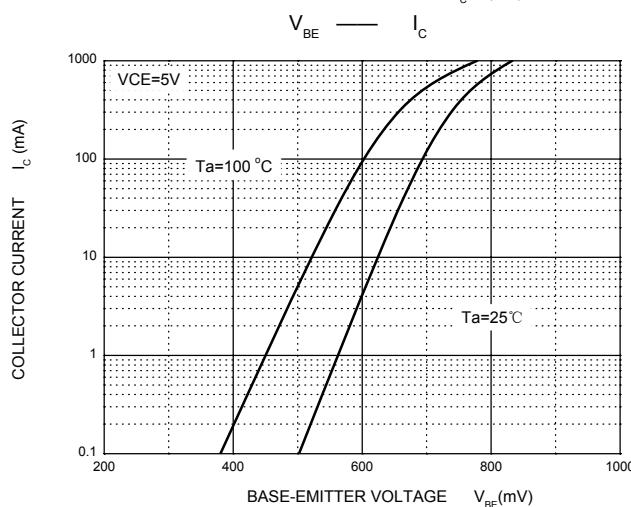
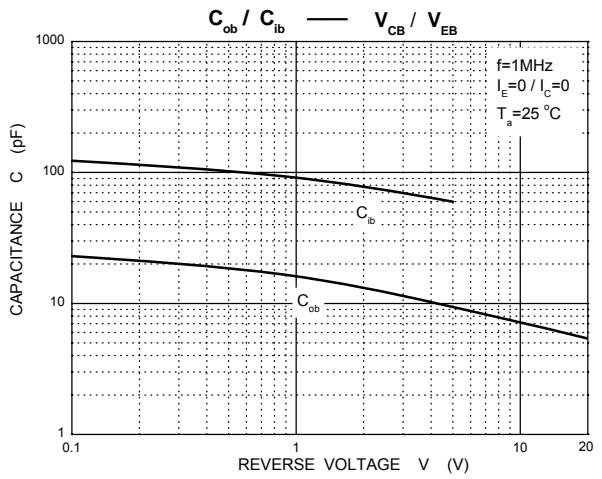
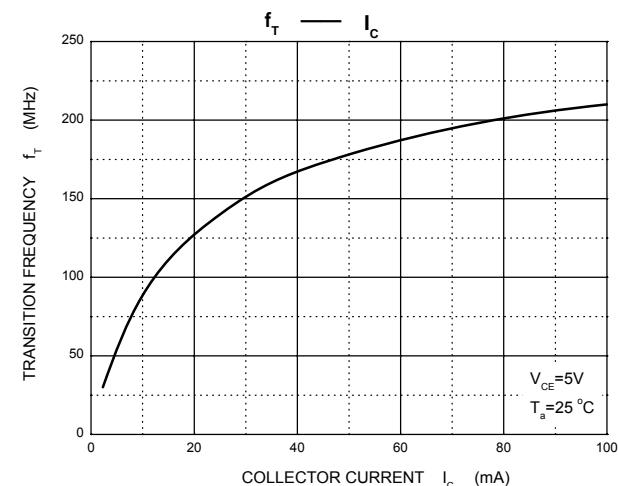
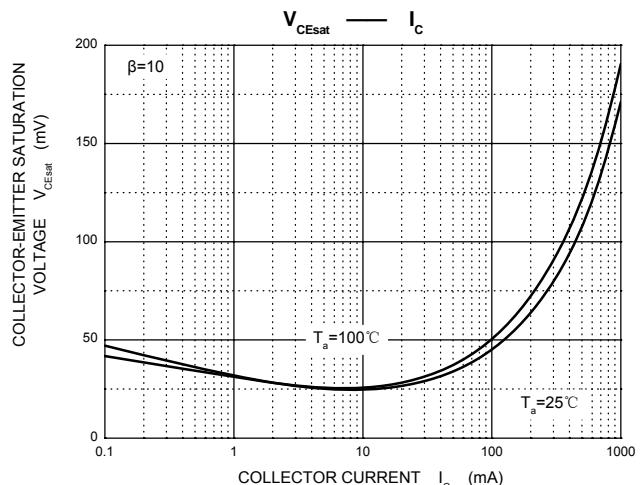
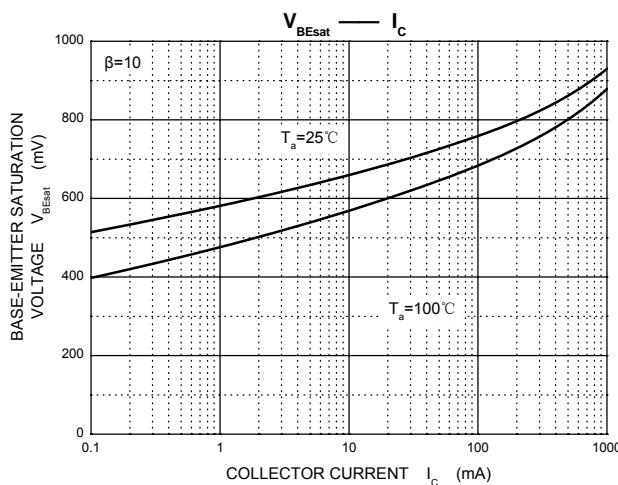
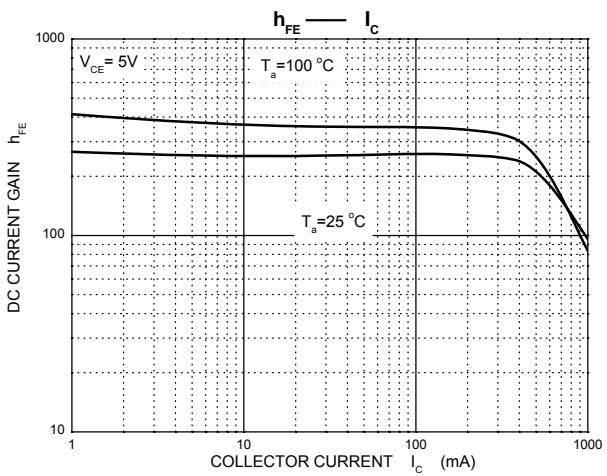
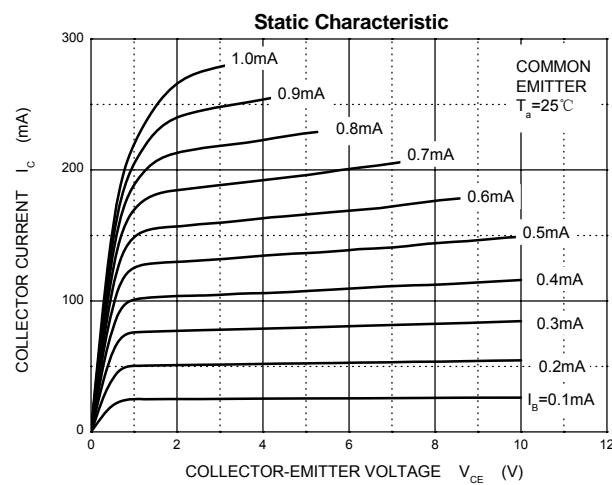
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _c =10μA,I _e =0		120			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _c =1mA,I _b =0	2SD667	80			V
			2SD667A	100			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _e =10μA,I _c =0		5			V
Collector cut-off current	I _{CBO}	V _{CB} =100V,I _e =0				10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V,I _c =0				10	μA
DC current gain	h _{FE(1)}	V _{CE} =5V,I _c =150mA	2SD667	60		320	
			2SD667A	60		320	
	h _{FE(2)}	V _{CE} =5V,I _c =500mA		30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =500mA,I _b =50mA				1	V
Base-emitter voltage	V _{BE}	V _{CE} =5V,I _c =150mA				1.5	V
Transition frequency	f _T	V _{CE} =5V,I _c =150mA			140		MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _e =0,f=1MHz			12		pF

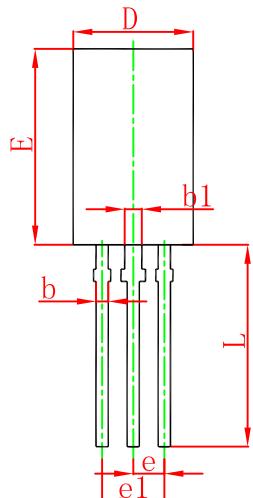
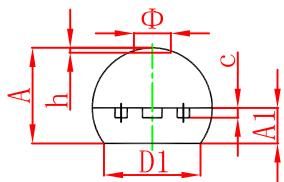
CLASSIFICATION OF h_{FE(1)}

Rank	B	C	D	
Range	2SD667	60-120	100-200	160-320
	2SD667A	60-120	100-200	160-320

Typical Characteristics

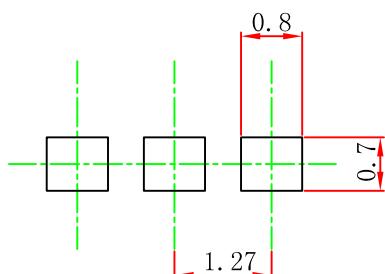


TO-92L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.700	4.100	0.146	0.161
A1	1.280	1.580	0.050	0.062
b	0.350	0.550	0.014	0.022
b1	0.600	0.800	0.024	0.031
c	0.350	0.450	0.014	0.018
D	4.700	5.100	0.185	0.201
D1	4.000		0.157	
E	7.800	8.200	0.307	0.323
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	13.800	14.200	0.543	0.559
Φ		1.600		0.063
h	0.000	0.300	0.000	0.012

TO-92L Suggested Pad Layout



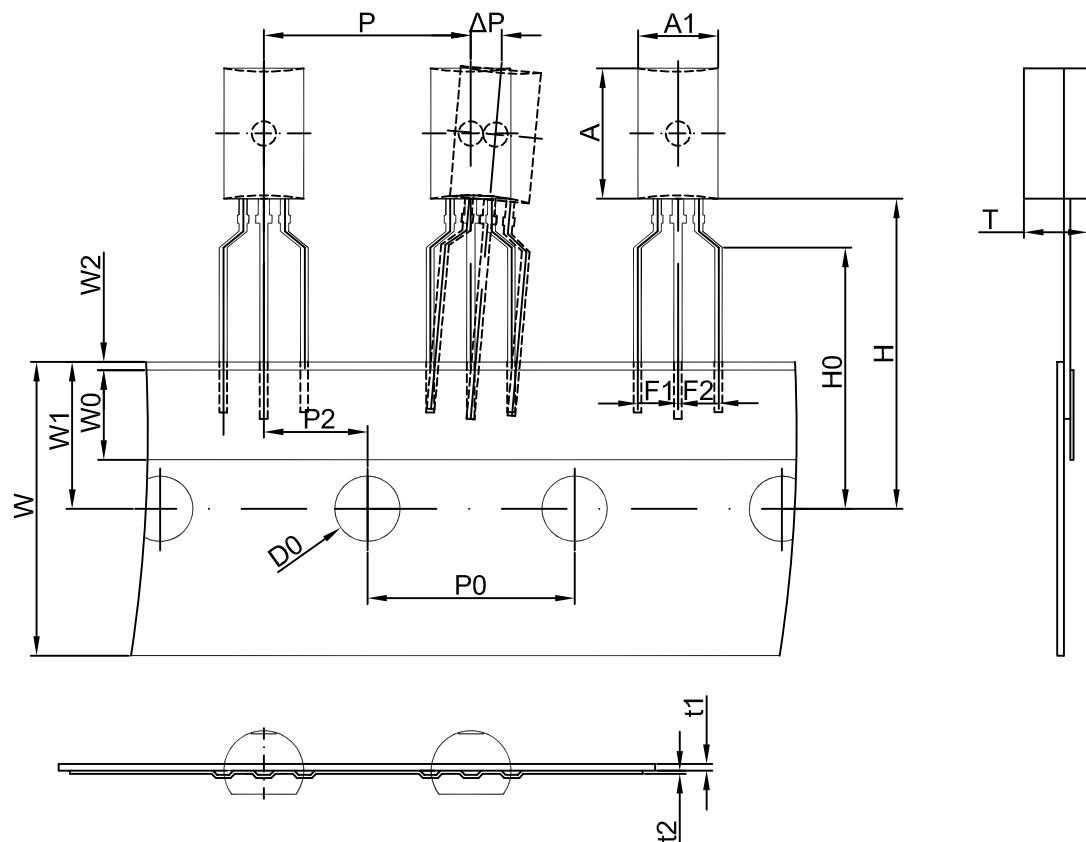
Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

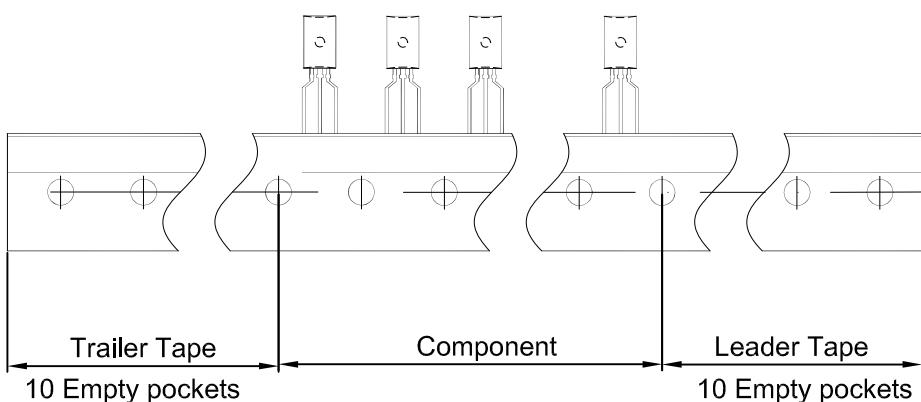
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TO-92L PACKAGE TAPEING DIMENSION



Dimensions are in millimeter								
A1	A	T	P	P0	P2	F1	F2	W
4.9±0.2	8.0±0.2	3.9±0.2	12.7±0.3	12.7±0.2	6.35±0.3	2.5±0.3	2.5±0.3	18.0+1.0/-0.5
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0±0.5	9.0±0.5	1.0 MAX.	19.0+2.0/-0	16.0±0.5	4.0±0.2	0.4±0.05	0.2±0.05	0 ± 1.0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92L	2000 pcs	333×203×42	20,000 pcs	493×400×264

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